

30V N-CHANNEL ENHANCEMENT MODE MOSFET

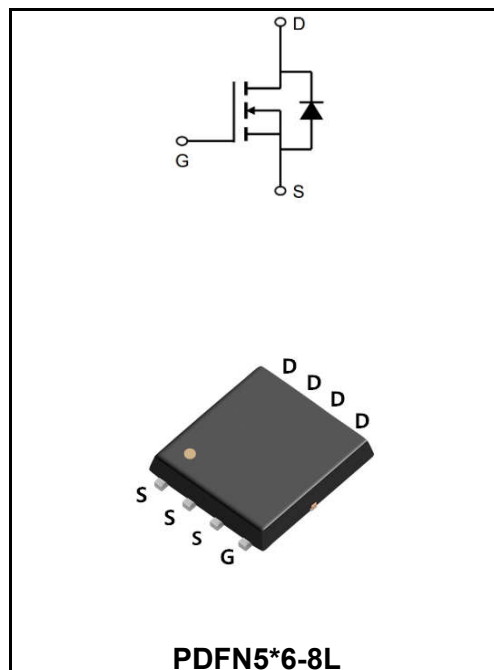
MAIN CHARACTERISTICS

I_D	80A
V_{DSS}	30V
$R_{DS(on)-typ}(@V_{GS}=10V)$	< 4.0mΩ (Type: 2.9mΩ)



Application

- ◆ Battery protection
- ◆ Load switch
- ◆ Uninterruptible power supply



Product Specification Classification

Part Number	Package	Marking	Pack
YFW80N03NF	PDFN5*6-8L	YFW 80N03NF XXXXX	5000PCS/Tape

Maximum Ratings at $T_c=25^{\circ}\text{C}$ unless otherwise specified

Characteristics	Symbols	Value	Units
Drain-Source Voltage	V_{DS}	30	V
Gate - Source Voltage	V_{GS}	± 20	V
Continuous Drain Current, $V_{GS} @ 10V^{1.6}$ @ $T_c=25^{\circ}\text{C}$	I_D	80	A
Continuous Drain Current, $V_{GS} @ 10V^{1.6}$ @ $T_c=100^{\circ}\text{C}$	I_D	65	A
Pulsed Drain Current ^{note1}	I_{DM}	400	A
Single Pulsed Avalanche Energy ^{note2}	E_{AS}	320	mJ
Avalanche Current	I_{AS}	45.8	A
Storage Temperature Range	T_{STG}	-55 to +175	$^{\circ}\text{C}$
Operating Junction Temperature Range	T_J	-55 to +175	$^{\circ}\text{C}$
Total Power Dissipation ⁴ @ $T_c=25^{\circ}\text{C}$	P_D	88	W
Total Power Dissipation ⁴ @ $T_A=25^{\circ}\text{C}$	P_D	44	W
Thermal Resistance Junction-ambient ¹	$R_{\theta JA}$	58	$^{\circ}\text{C/W}$
Thermal Resistance Junction-Ambient 1 (t ≤ 10s)	$R_{\theta JA}$	20	$^{\circ}\text{C/W}$
Thermal Resistance, Junction to Case ¹	$R_{\theta JC}$	2.3	$^{\circ}\text{C/W}$

Maximum Ratings at Tc=25°C unless otherwise specified

Characteristics	Test Condition	Symbols	Min	Typ	Max	Units
Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	V(BR)DSS	30	-	-	V
Zero Gate Voltage Drain Current	$V_{DS}=30V, V_{GS}=0V$	I_{DSS}	-	-	1.0	μA
Gate to Body Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	I_{GSS}	-	-	±100	nA
Gate -Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	V_{GS(th)}	1.0	1.5	2.5	V
Static Drain-Source On-Resistance	$V_{GS}=10V, I_D=24A$	R_{DS(ON)}	-	2.9	4.0	mΩ
	$V_{GS}=4.5V, I_D=12A$		-	5.3	6.5	
Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1MHz$	R_g	-	-	3.3	Ω
Forward Transconductance	$V_{DS}=10V, I_D=10A$	g_{FS}	-	15.5	-	S
Input Capacitance	$V_{DS}=25V$ $V_{GS}=0V$ $f=1.0MHz$	C_{iss}	-	2200	-	pF
Output Capacitance		C_{oss}	-	280	-	
Reverse Transfer Capacitance		C_{rss}	-	177	-	
Total Gate Charge	$V_{DS}=15V$ $I_D=24A$ $V_{GS}=10V$	Q_g	-	42	-	nC
Gate-Source Charge		Q_{gs}	-	4	-	
Gate-Drain("Miller") Charge		Q_{gd}	-	13	-	
Turn-on delay time	$V_{DS}=15V$ $I_D=15A$ $R_{GEN}=3.3\Omega$ $V_{GS}=10V$	t_{d(on)}	-	12.6	-	ns
Turn-on Rise Time		T_r	-	19.5	-	
Turn-Off Delay Time		t_{d(OFF)}	-	42.8	-	
Turn-Off Fall Time		t_f	-	13.2	-	
Continuous Source Current ^{1,5}	$V_G=V_D=0V$, Force Current	I_S	-	-	100	A
Pulsed Source Current ^{2,6}		I_{SM}	-	-	400	A
Diode Forward Voltage ²	$V_{GS}=0V, I_S=30A$	V_{SD}	-	-	1.2	V
Body Diode Reverse Recovery Time	$IF=30A, dI/dt=100A/\mu s$	t_{rr}	-	19	-	ns
Body Diode Reverse Recovery Charge		Q_{rr}	-	11	-	nC

Note :

1.The data tested by surface mounted on a 1 inch 2 FR-4 board with 2OZ copper.

2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$

3.The EAS data shows Max. rating . The test condition is VDD =25V,V GS =10V,L=0.1mH,I AS =45.8A

4.The power dissipation is limited by 175°C junction temperature

5.The data is theoretically the same as I D and I DM , in real applications , should be limited by total power dissipation.

6.Package limitation current is 85A

Ratings and Characteristic Curves

Typical Characteristics

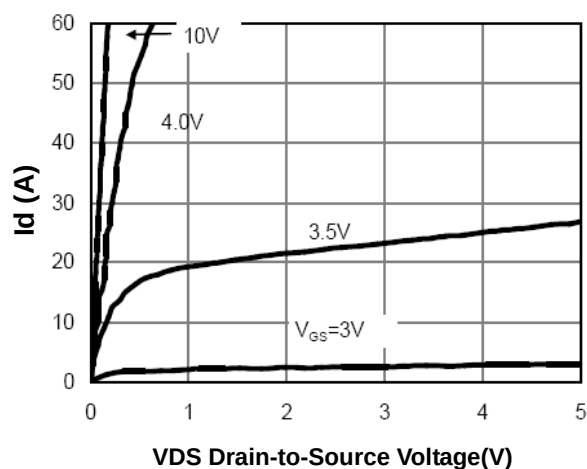


Figure 1. Output Characteristics

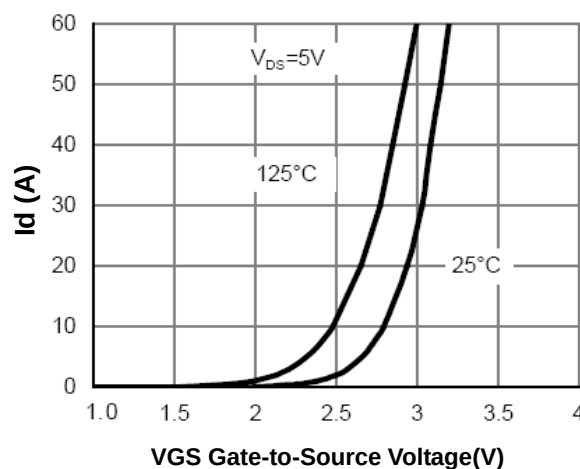


Figure 2. Transfer Characteristics

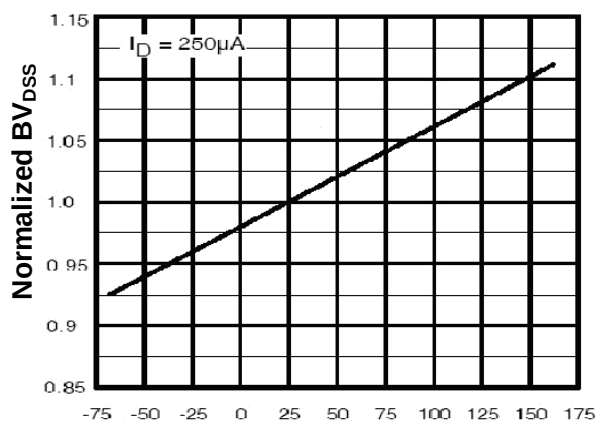


Figure 3. Max BV_{DS} vs Junction Temperature

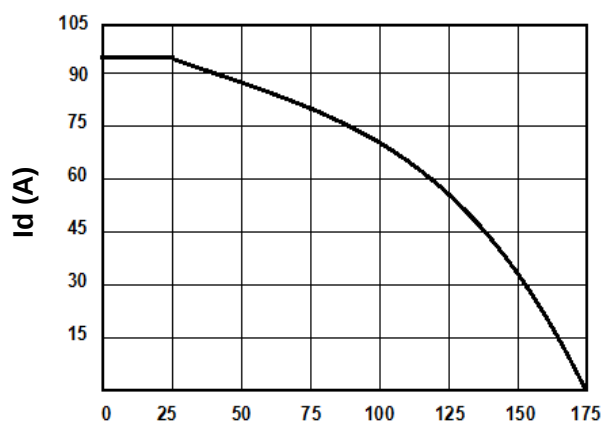


Figure 4. Drain Current

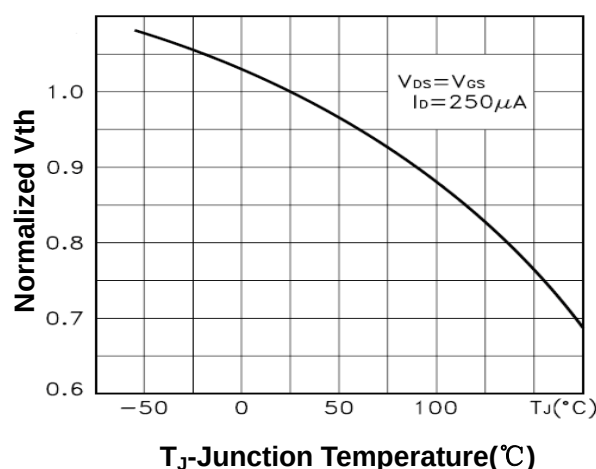


Figure 5. $V_{GS(th)}$ vs Junction Temperature

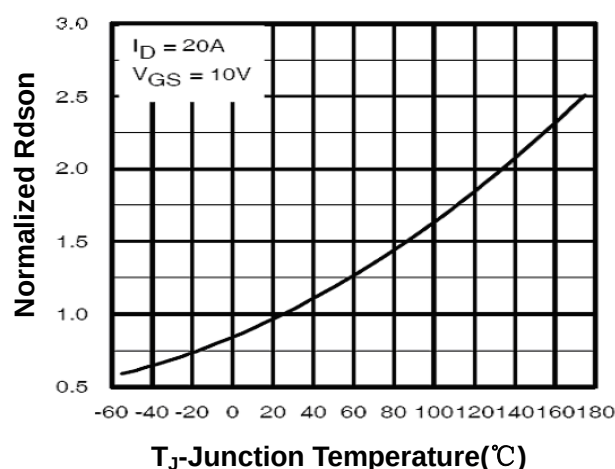


Figure 6. $R_{DS(on)}$ vs Junction Temperature

Ratings and Characteristic Curves

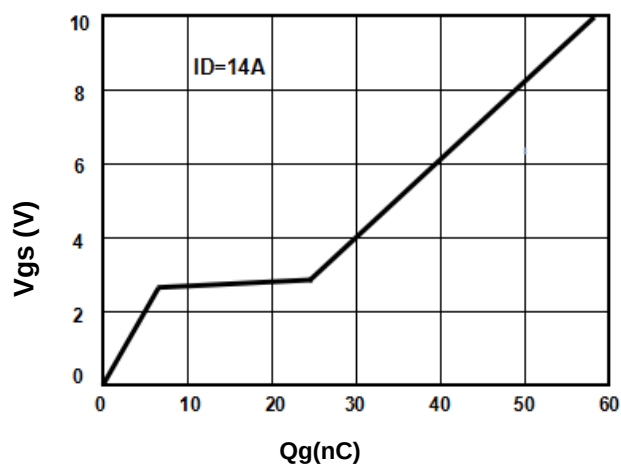


Figure 7. Gate Charge Waveforms

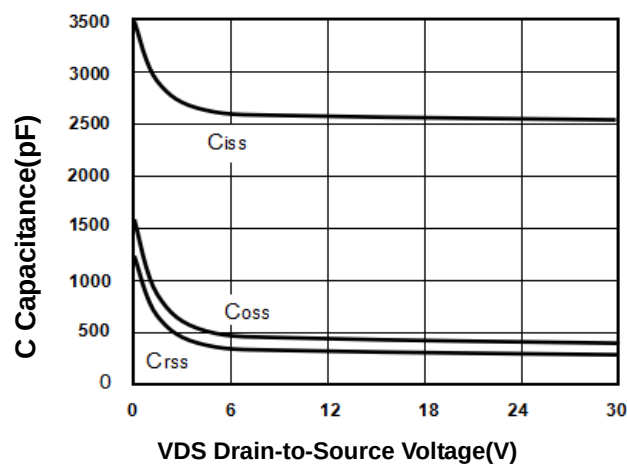


Figure 8. Capacitance

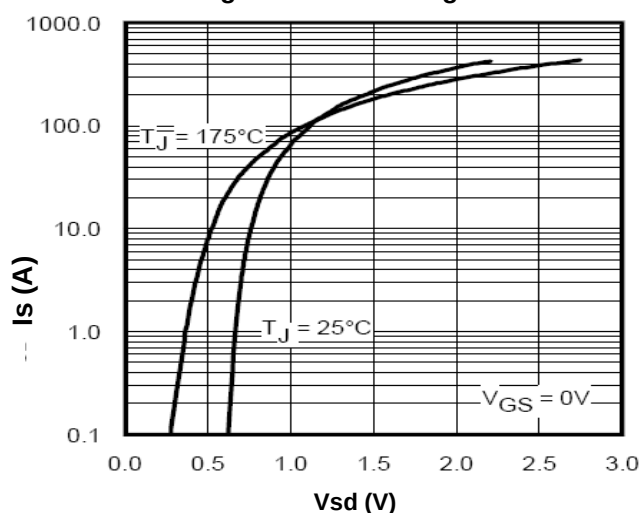


Figure 9. Body-Diode Characteristics

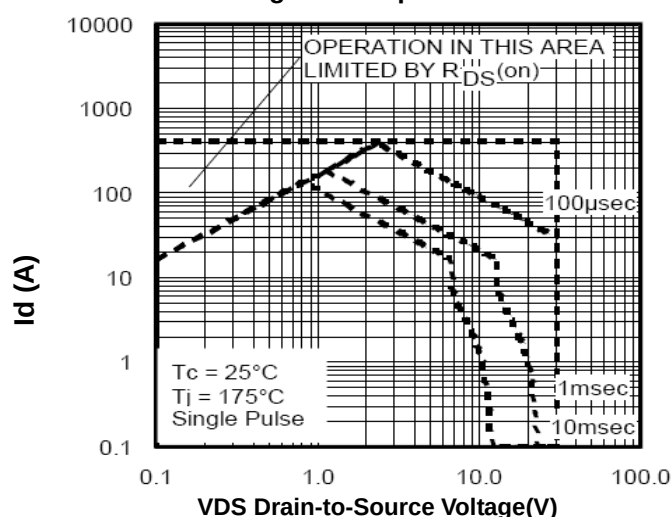


Figure 10. Maximum Safe Operating Area

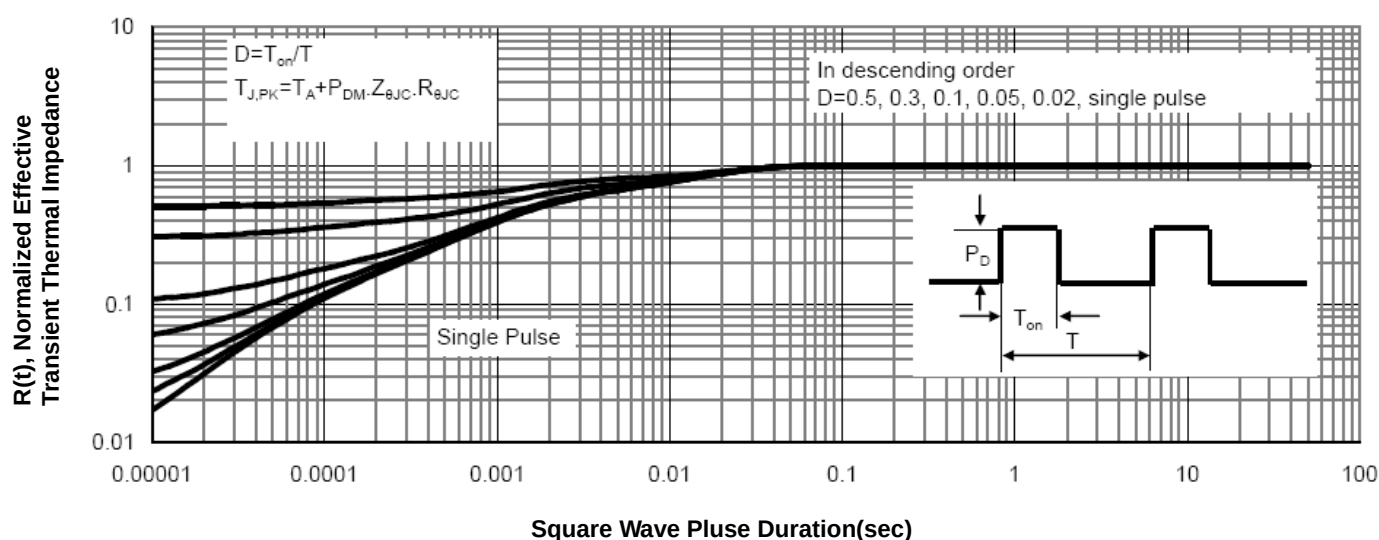
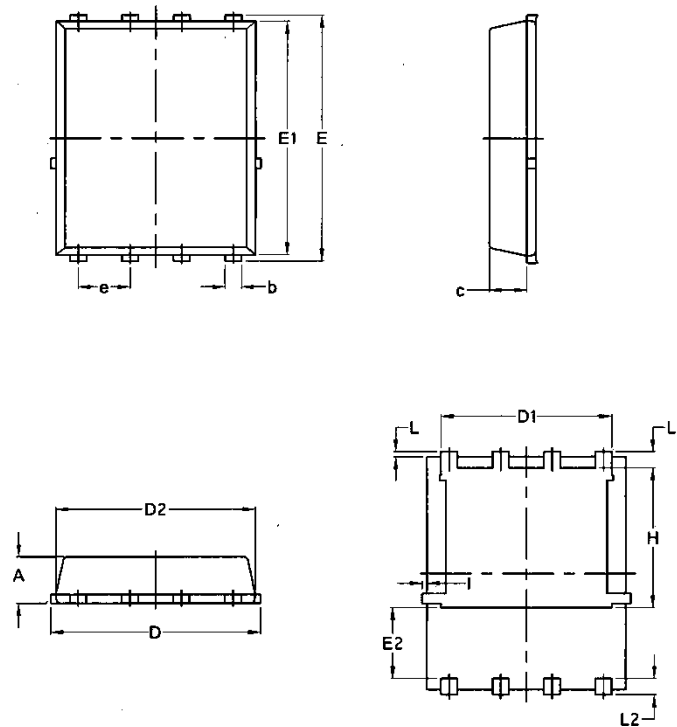


Figure 11. Normalized Maximum Transient Thermal Impedance

PDFN5*6-8L



Symbol	Common			
	mm		Inch	
	Mim	Max	Min	Max
A	1.03	1.17	0.0406	0.0461
b	0.34	0.48	0.0134	0.0189
c	0.824	0.0970	0.0324	0.082
D	4.80	5.40	0.1890	0.2126
D1	4.11	4.31	0.1618	0.1697
D2	4.80	5.00	0.1890	0.1969
E	5.95	6.15	0.2343	0.2421
E1	5.65	5.85	0.2224	0.2303
E2	1.60	/	0.0630	/
e	1.27 BSC		0.05 BSC	
L	0.05	0.25	0.0020	0.0098
L1	0.38	0.50	0.0150	0.0197
L2	0.38	0.50	0.0150	0.0197
H	3.30	3.50	0.1299	0.1378
I	/	0.18	/	0.0070